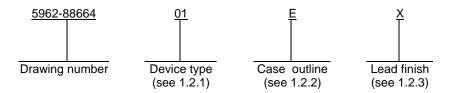
						F	REVISION	SNC										
LTR			DESCRIPTION				DATE (YR-MO-DA)				APPROVED							
А	Make correction to	the H _{FE}	the H _{FE} test as specified under table I.			ole I	ro		02-06-25			R. MONNIN						
REV SHEET REV SHEET REV STATUS	L FIRST SHEET OF	THIS DRA		G HAS E	BEEN A 1	REPLA A 2	ACED.	A 4	A 5	A 6	A 7	A 8						
THE ORIGINA REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A		REV SHEE	ET ARED		A 1	A	A		5	6	7		Y CEI	NTER	R COL	UMB	US	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA		REV SHEE PREPA CHAR	ET ARED RLES	BY E. BES	A 1	A	A		5	6 EFEN	7 SE SI COL	8	JS, O	HIO 4	43216		US	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR. THIS DRAWI FOR U DEPA	INDARD OCIRCUIT AWING ING IS AVAILABLE USE BY ALL ARTMENTS	REV SHEE PREPA CHAR	ARED RLES	BY E. BES BY NIN	A 1 SORE	A	A	4 MIC	DE DE	6 EFEN:	FE SI COLI	8 JPPL UMBL	JS, O vw.ds	HIO de cc.dla	43216 a.mil ———	REN	 T, NF	PN
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR. THIS DRAWI FOR L DEPA AND AGE	INDARD OCIRCUIT AWING	REV SHEE PREPA CHAR CHECI RAY I	ARED RLES	BY E. BES NIN	A 1 SORE	A 2	A	4 MIC	DE DE	6 EFEN:	FE SI COLI	JPPL UMBU :://ww	JS, O vw.ds	HIO de cc.dla	43216 a.mil ———	REN	 T, NF	N.
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR. THIS DRAWII FOR L DEPA AND AGE DEPARTME	INDARD DCIRCUIT AWING ING IS AVAILABLE USE BY ALL ARTMENTS NCIES OF THE	REV SHEE PREPA CHAR CHECI RAY I	ARED EMONN ROVEDHAEL A	BY E. BES NIN D BY A. FRYE	A 1 SORE	A 2	A	4 MIC	DE ROC ANSIS	6 EFEN: CIRCUSTOF	FE SI COLI	JPPL UMBU D://ww LINE/ RAY,	JS, O vw.ds	HIO (cc.dla	43216 a.mil ———	REN' SILIO	T, NF	N .

1. SCOPE

- 1.1 <u>Scope</u>. This drawing describes device requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A.
 - 1.2 Part or Identifying Number (PIN). The complete PIN is as shown in the following example:



1.2.1 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

 Device type
 Generic number
 Circuit function

 01
 SG3081
 High current NPN transistor array

1.2.2 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
Е	GDIP1-T16 or CDIP2-T16	16	Dual-in-line

- 1.2.3 Lead finish. The lead finish is as specified in MIL-PRF-38535, appendix A.
- 1.3 Absolute maximum ratings. 1/

Collector-to-emitter voltage (V _{CEO})	16 V dc
Collector-to-base voltage (V _{CBO})	20 V dc
Collector-to-substrate voltage (V _{CSO})	20 V dc
Emitter-to-base voltage (V _{EBO})	5.0 V dc
Collector current (I _C)	100 mA
Base emitter (I _B)	20 mA
Power dissipation (P _D): Any one transistor Total package	500 mW 750 mW <u>2</u> /
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	-65°C to +150°C +300°C

1.4 Recommended operating conditions.

Ambient operating temperature range (T_A)-55°C to +125°C

- 1/ Voltage and current ratings applies to each transistor in the array.
- $\underline{2}$ / Derate above T_A = +25°C at 6.67 mW/°C.

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2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 -- Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 -- List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein. Product built to this drawing that is produced by a Qualified Manufacturer Listing (QML) certified and qualified manufacturer or a manufacturer who has been granted transitional certification to MIL-PRF-38535 may be processed as QML product in accordance with the manufacturers approved program plan and qualifying activity approval in accordance with MIL-PRF-38535. This QML flow as documented in the Quality Management (QM) plan may make modifications to the requirements herein. These modifications shall not affect form, fit, or function of the device. These modifications shall not affect the PIN as described herein. A "Q" or "QML" certification mark in accordance with MIL-PRF-38535 is required to identify when the QML flow option is used.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535, appendix A and herein.
 - 3.2.1 Case outline. The case outline shall be in accordance with 1.2.2 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.

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TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions $\underline{1}/$ -55°C \leq T _A \leq +125°C unless otherwise specified	Group A subgroups	Device type	Li	mits	Unit
					Min	Max	
Collector-to-base breakdown voltage	BV _{CBO}	$I_C = 500 \mu A, I_E = 0 mA$	1,2,3	01	20		V
Collector-to-emitter breakdown voltage	BV _{CEO}	$I_C = 500 \mu A, I_B = 0 mA$	1,2,3	01	16		V
Collector-to-substrate breakdown voltage	BV _{CSO}	$I_C = 500 \mu A, I_E = 0 mA,$ $I_B = 0 mA$	1,2,3	01	20		V
Emitter-to-base breakdown voltage	BV _{EBO}	I _C = 500 μA	1,2,3	01	5.0		V
DC forward current transfer ratio	H _{FE}	$V_{CE} = 5.0 \text{ V}, I_{C} = 30 \text{ mA},$ $T_{A} = +25^{\circ}\text{C}$	1	01	50		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA},$ $T_{A} = +25^{\circ}\text{C}$			40		
Base-to-emitter saturation voltage	V _{BE} (sat)	I _C = 30 mA, I _B = 1.0 mA	1	01		1.0	V
			2,3			1.2	
Collector-to-emitter saturation voltage	V _{CE} (sat)	I _C = 30 mA, I _B = 1.0 mA	1	01		0.5	V
			2,3			0.9	
		$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	1			0.7	
			2,3		_	1.1	
Collector cutoff current	I _{CEO}	V _{CE} = 10 V, I _B = 0 mA	1	01		10	μА
			2,3			70	
		V _{CB} = 10 V, I _E = 0 mA	1,2,3			6.0	

 $\underline{1}$ / Parameters apply to each transistor in the array.

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Device type	01
Case outline	Е
Terminal number	Terminal symbol
1	COLLECTOR 1
2	COLLECTOR 2
3	BASE 2
4	COLLECTOR 3
5	SUBSTRATE (see note 1)
6	BASE 3
7	COLLECTOR 4
8	BASE 4
9	COLLECTOR 5
10	BASE 5
11	BASE 6
12	COLLECTOR 6
13	BASE 7
14	COLLECTOR 7
15	EMITTER (see note 2)
16	BASE 1

NOTES:

- 1. The substrate pin must be connected to the most negative dc potential, which should also be a good ac ground, for proper isolation between transistors.

 2. The emitter is common to all seven transistors in the array.

FIGURE 1. <u>Terminal connections</u>.

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- 3.5 <u>Marking</u>. Marking shall be in accordance with MIL-PRF-38535, appendix A. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103 (see 6.6 herein). For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device.
- 3.5.1 <u>Certification/compliance mark</u>. A compliance indicator "C" shall be marked on all non-JAN devices built in compliance to MIL-PRF-38535, appendix A. The compliance indicator "C" shall be replaced with a "Q" or "QML" certification mark in accordance with MIL-PRF-38535 to identify when the QML flow option is used.
- 3.6 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-PRF-38535, appendix A and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 Notification of change. Notification of change to DSCC-VA shall be required in accordance with MIL-PRF-38535, appendix A.
- 3.9 <u>Verification and review</u>. DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 <u>Quality conformance inspection</u>. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
 - 4.3.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 4, 5, 6, 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

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TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)
Interim electrical parameters (method 5004)	1
Final electrical test parameters (method 5004)	1*,2,3
Group A test requirements (method 5005)	1,2,3
Groups C and D end-point electrical parameters (method 5005)	1

^{*} PDA applies to subgroup 1.

4.3.2 Groups C and D inspections.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Steady-state life test conditions, method 1005 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535, appendix A.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.2 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Supply Center Columbus when a system application requires configuration control and the applicable SMD. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

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6.5 Comments. Comments on this drawing should be direct (614) 692-0547.	ted to DSCC-VA, (Columbus, Ohio 43216-500	0, or telephone		
6.6 Approved sources of supply. Approved sources of supply are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted					
by DSCC-VA.					
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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 02-06-25

Approved sources of supply for SMD 5962-88664 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard	Vendor	Vendor
microcircuit drawing	CAGE	similar
PIN 1/	number	PIN 2/
5962-8866401EA	34333	SG3081J/883B

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>Z</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGEVendor namenumberand address

34333 Microsemi Integrated Products 11861 Western Avenue

Garden Grove, CA 92641-1816

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.